ELECTRONIC DEVICES & CIRCUITS (19APCO403T)

(Electronics & Communication Engineering)

Time.	3	Hours		

Max Marks: 70

		PART-A(Compulsory)	(10*2=20)	M)
,	\	Answer the following	UNIT	Marks
1	\sqrt{a}	Draw the V-1 characteristics of UJT	I	2
-	(d	What is the difference between DIAC and TRIAC	I	2
-	70)	Draw the waveforms of output of full wave rectifier with & without filters	II	2
-	(4)	What is the difference between L-section & pi filters?	II	2
	Ve)	What is Bias Compensation?	III	2
	7	What is the difference between CC and CE configurations?	Ш	2
	$J_{g)}$	What is the difference between Enhancement mode & Depletion mode?	IV	2
	(h)	What is the difference between n-channel & p-channel JFET?	IV	2
11	i	Explain how JFET acts like a switch.	V	2
	i	What are the different biasing circuits?	V	2

PART-B

(5*10=50 M)

Answer One Full Question from each unit; All questions carry EQUAL marks.

Explain how BJT acts as a switch and Amplifier

	UNIT-I	
2	Explain the construction, Operation and Characteristics of Tunnel diode with the help of Energy band diagram.	10 M
,	(OR)	17/A
3	What is SCR? Explain its operation and V-I characteristics	10 M
	UNIT-II	
4	Explain in detail the operation of Clipping and Clamping circuits with waveforms	10 M
1	(OR)	
5	Explain the construction, operation, and characteristics of Zener diode.	10 M
/	UNIT-III	
6.	Compare and differentiate between the different configurations of BJT	10 M

	UNIT-IV	
8	Explain the construction, principle of operation & applications of JFET	10 M
	[20] [4] [4] [4] [4] [4] [4] [4] [4] [4] [4	

10 M

V 9.	Explain the construction, principle of operation & applications of MOSFET	10 M
1	UNIT-V	The state of the s
40	Explain how FET acts a switch and Amplifier.	10 M
	(OR)	
11.	Explain in detail the different biasing circuits used using MOSFET	10 M